

## CLAIMS

What is claimed is:

- 1 1. A data processing system comprising:  
2 a bus coupling components in the data processing system;  
3 a display coupled to the bus;  
4 external memory coupled to the bus; and  
5 a processor coupled to the bus and comprising an electronic assembly  
6 including at least one integrated circuit package comprising:  
7 a substrate;  
8 a die positioned on a surface of the substrate, the die having a  
9 surface;  
10 an adhesion layer of metal formed on the surface;  
11 a solder-wettable layer formed on the adhesion layer;  
12 a lid positioned over the die; and  
13 a solderable thermally conductive element coupling the solder-  
14 wettable layer and the lid.
- 1 2. The data processing system recited in claim 1 wherein the solderable  
2 thermally conductive element comprises material, including one or more alloys,  
3 from the group consisting of tin, bismuth, silver, indium, and lead.
- 1 3. The data processing system recited in claim 1 wherein the substrate is an  
2 organic substrate and wherein the die is coupled to the substrate through a land grid  
3 array.

- 1 4. A method comprising:  
2 forming at least one metal layer on a surface of a die;  
3 mounting the die on a substrate;  
4 applying solder material to the at least one metal layer;  
5 positioning a surface of a lid adjacent the solder material; and  
6 melting the solder material to physically couple the lid to the die.
- 1 5. The method recited in claim 4 wherein, in applying the solder material, the  
2 solder material has a relatively high thermal conductivity and a relatively low  
3 melting point.
- 1 6. The method recited in claim 4 wherein, in mounting the die on the substrate,  
2 the substrate comprises organic material having a relatively high thermal coefficient  
3 of expansion relative to that of the die.
- 1 7. The method recited in claim 4 and further comprising forming at least one  
2 metal or organic layer on the surface of the lid prior to positioning the surface of the  
3 lid.
- 1 8. A method comprising:  
2 forming an adhesion layer of metal on a surface of a die;  
3 forming a solder-wettable layer on the adhesion layer;  
4 mounting the die on a substrate;  
5 applying solder material to the solder-wettable layer;  
6 positioning a surface of a lid adjacent the solder material; and  
7 melting the solder material to physically couple the lid to the die.

- 1 9. The method recited in claim 8 wherein, in forming the adhesion layer, the  
2 adhesion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.
- 1 10. The method recited in claim 8 wherein, in forming the solder-wettable layer,  
2 the solder-wettable layer comprises one of nickel and gold.
- 1 11. The method recited in claim 8 wherein, in applying the solder material, the  
2 solder material has a relatively high thermal conductivity and a relatively low  
3 melting point.
- 1 12. The method recited in claim 8 wherein, in mounting the die on the substrate,  
2 the substrate comprises organic material having a relatively high thermal coefficient  
3 of expansion relative to that of the die.
- 1 13. The method recited in claim 8 wherein, in positioning the surface of the lid,  
2 the lid comprises material from the group consisting of copper and aluminum-  
3 silicon-carbide.
- 1 14. The method recited in claim 8 wherein, in applying solder material, the  
2 solder material comprises material, including one or more alloys, from the group  
3 consisting of tin, bismuth, silver, indium, and lead.
- 1 15. The method recited in claim 8 and further comprising forming at least one  
2 metal or organic layer on the surface of the lid prior to positioning the surface of the  
3 lid.

1 16. The method recited in claim 15 wherein, in forming the at least one metal or  
2 organic layer, the at least one metal or organic layer comprises one of nickel and  
3 gold.

1 17. The method recited in claim 8 and further comprising:  
2 forming a diffusion layer between the adhesion layer and the solder-wettable  
3 layer.

1 18. The method recited in claim 17 wherein, in forming the diffusion layer, the  
2 diffusion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.

1 19. A method comprising:  
2 forming an adhesion layer of metal on a back surface of a die;  
3 forming a solder-wettable layer on the adhesion layer;  
4 mounting another surface of the die on a substrate; and  
5 applying solder material to the solder-wettable layer.

1 20. The method recited in claim 19 wherein, in forming the adhesion layer, the  
2 adhesion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.

1 21. The method recited in claim 19 wherein, in forming the solder-wettable  
2 layer, the solder-wettable layer comprises one of nickel and gold.

1 22. The method recited in claim 19 wherein, in applying the solder material, the  
2 solder material comprises material, including one or more alloys, from the group  
3 consisting of tin, bismuth, silver, indium, and lead.

1 23. The method recited in claim 19 and further comprising:  
2 forming a diffusion layer between the adhesion layer and the solder-wettable  
3 layer.

1 24. The method recited in claim 23 wherein, in forming the diffusion layer, the  
2 diffusion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.

1 25. A method comprising:  
2 forming an adhesion layer of metal on a surface of a die; and  
3 forming a solder-wettable layer on the adhesion layer.

1 26. The method recited in claim 25 wherein, in forming the adhesion layer, the  
2 adhesion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.

1 27. The method recited in claim 25 wherein, in forming the solder-wettable  
2 layer, the solder-wettable layer comprises one of nickel and gold.

1 28. The method recited in claim 25 and further comprising:  
2 forming a diffusion layer between the adhesion layer and the solder-wettable  
3 layer.

1 29. The method recited in claim 28 wherein, in forming the diffusion layer, the  
2 diffusion layer comprises material, including one or more alloys, from the group  
3 consisting of titanium, chromium, zirconium, nickel, vanadium, and gold.